

# P-Type Zinc Oxide Nanowires

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## TECHNOLOGY DESCRIPTION

Researchers at UC San Diego have developed a method of p-doping zinc oxide nanostructures. This wideband gap semiconductor has been difficult to p-dope. The realization of p-doping enables complimentary doping and novel electronic devices, such as transistors, vertical FETs, possibly UV, visible, and white LEDs.

## INTELLECTUAL PROPERTY INFO

The method is in early-stage development and is available for licensing. Patents pending.

## PATENT STATUS

Country	Type	Number	Dated	Case
United States Of America	Issued Patent	8,426,224	04/23/2013	2007-086

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## OTHER INFORMATION

### CATEGORIZED AS

- **Semiconductors**
  - Design and Fabrication
  - Processing and Production

### RELATED CASES

2007-086-0